

Silicon NPN Power Transistors

2N5838 2N5839 2N5840

DESCRIPTION

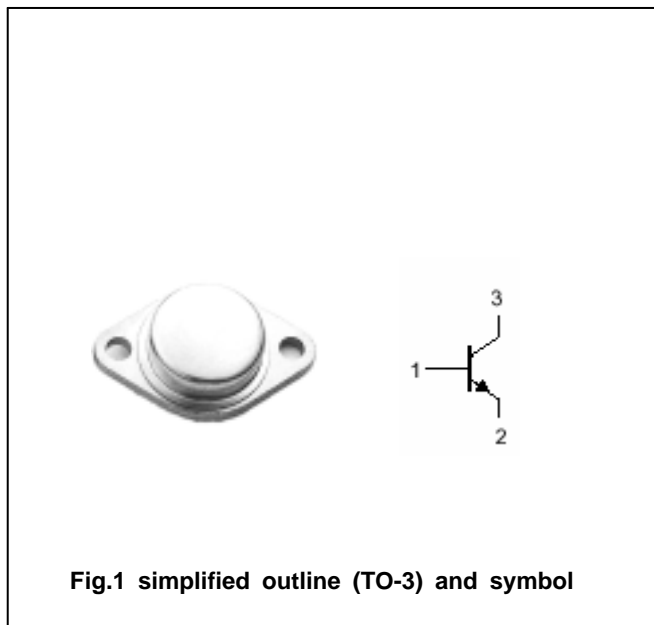
- With TO-3 package
- Low collector saturation voltage
- High breakdown voltage

APPLICATIONS

- For use in switching power supply and other inductive switching circuits.

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5838	275	V
		2N5839	300	
		2N5840	375	
V _{CEO}	Collector-emitter voltage	2N5838	250	V
		2N5839	275	
		2N5840	350	
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
P _D	Total power dissipation	T _C =25	100	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.25	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	2N5838	I _C =0.1A ; I _B =0	250			V
		2N5839		275			
		2N5840		350			
V _{CEsat}	Collector-emitter saturation voltage		I _C =2A; I _B =0.4A			0.8	V
V _{BEsat}	Base-emitter saturation voltage		I _C =2A; I _B =0.4A			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CBO} ; I _E =0			1.0	mA
I _{CEV}	Collector cut-off current		V _{CE} = Rated V _{CEQ} ; V _{BE(off)} =1.5V			1.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			1.0	mA
h _{FE}	DC current gain	2N5838	I _C =3A ; V _{CE} =3V	8		40	
		2N5839/5840	I _C =2A ; V _{CE} =3V	10		50	
f _T	Transition frequency		I _C =1A ; V _{CE} =10V; f=1.0MHz	5			MHz

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PACKAGE OUTLINE

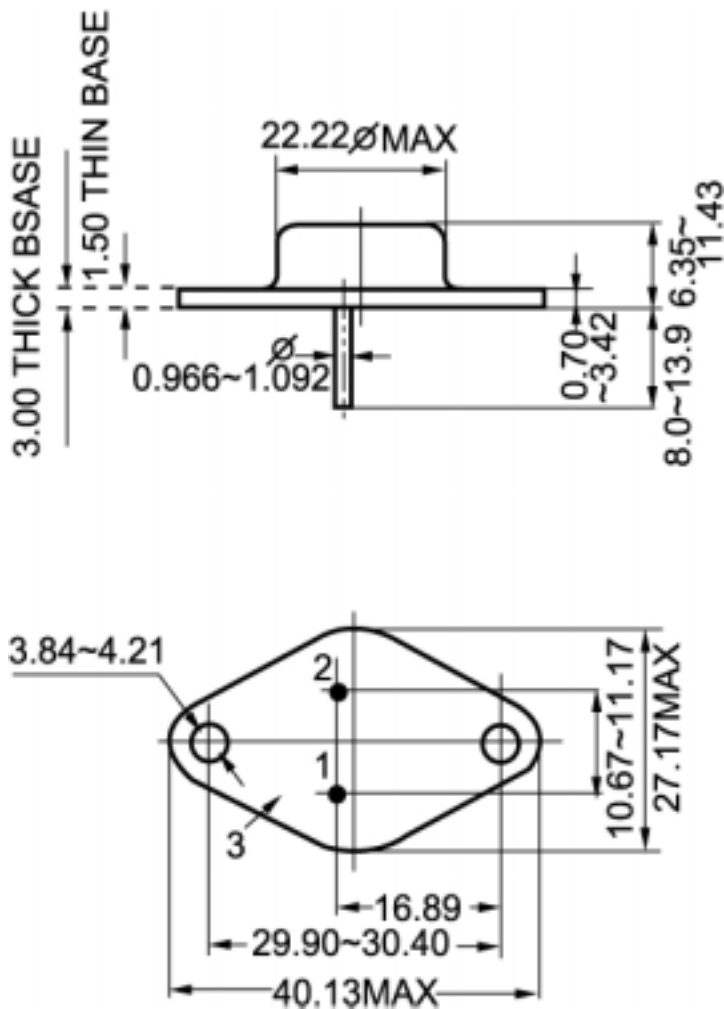


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)